Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SAI, SPDIF, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	132
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f777iit6

- Up to 28 communication interfaces
  - Up to 4 I^2C interfaces (SMBus/PMBus)
  - Up to 4 USARTs/4 UARTs (12.5 Mbit/s, ISO7816 interface, LIN, IrDA, modem control)
  - Up to 6 SPIs (up to 54 Mbit/s), 3 with muxed simplex I^2S for audio
  - 2 x SAIs (serial audio interface)
  - 3 × CANs (2.0B Active) and 2x SDMMCs
  - SPDIFRX interface
  - HDMI-CEC
  - MDIO slave interface
- Advanced connectivity
  - USB 2.0 full-speed device/host/OTG controller with on-chip PHY
  - USB 2.0 high-speed/full-speed device/host/OTG controller with dedicated DMA, on-chip full-speed PHY and ULPI
  - 10/100 Ethernet MAC with dedicated DMA: supports IEEE 1588v2 hardware, MII/RMII
- 8- to 14-bit camera interface up to 54 Mbyte/s
- Cryptographic acceleration: hardware acceleration for AES 128, 192, 256, triple DES, HASH (MD5, SHA-1, SHA-2), and HMAC
- True random number generator
- CRC calculation unit
- RTC: subsecond accuracy, hardware calendar
- 96-bit unique ID

Table 1. Device summary

Reference	Part number
STM32F777xx	STM32F777BI, STM32F777II, STM32F777NI, STM32F777VI, STM32F777ZI
STM32F778Ax	STM32F778AI
STM32F779xx	STM32F779AI, STM32F779BI, STM32F779II, STM32F779NI

List of tables

Table 6. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary output	Max interface clock (MHz)	Max timer clock (MHz)(1)
Advanced -control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	108	216
General purpose	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	54	108/216
	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	54	108/216
	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	108	216
	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	108	216
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	54	108/216
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	54	108/216
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	54	108/216

1. The maximum timer clock is either 108 or 216 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.

Table 10. STM32F777xx, STM32F778Ax and STM32F779xx pin and ball definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F777xx						STM32F778Ax STM32F779xx									
LQFP100	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216	WLCSP180[1]	LQFP176	LQFP208	TFBGA216						
-	-	C13	134	157	C13	D3	134	157	C13	PI3	I/O	FT	-	TIM8_ETR, SPI2_MOSI/I2S2_SD, FMC_D27, DCMI_D10, EVENTOUT	-
-	-	D9	135	-	F9	-	135	-	F9	VSS	S	-	-	-	
-	-	C9	136	158	E10	-	136	158	E10	VDD	S	-	-	-	--
76	109	A14	137	159	A14	A3	137	159	A14	PA14(JTCK-SWCLK)	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
77	110	A13	138	160	A13	F8	138	160	A13	PA15(JTDI)	I/O	FT	-	JTDI, TIM2_CH1/TIM2_ETR, HDMI_CEC, SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, SPI6_NSS, UART4_RTS, CAN3_TX, UART7_TX, EVENTOUT	-
78	111	B14	139	161	B14	B4	139	161	B14	PC10	I/O	FT	-	DFSDM1_CKIN5, SPI3_SCK/I2S3_CK, USART3_TX, UART4_TX, QUADSPI_BK1_IO1, SDMMC1_D2, DCMI_D8, LCD_R2, EVENTOUT	-
79	112	B13	140	162	B13	C4	140	162	B13	PC11	I/O	FT	-	DFSDM1_DATIN5, SPI3_MISO, USART3_RX, UART4_RX, QUADSPI_BK2_NCS, SDMMC1_D3, DCMI_D4, EVENTOUT	-
80	113	A12	141	163	A12	D4	141	163	A12	PC12	I/O	FT	-	TRACED3, SPI3_MOSI/I2S3_SD, USART3_CK, UART5_TX, SDMMC1_CK, DCMI_D9, EVENTOUT	-

Table 10. STM32F777xx, STM32F778Ax and STM32F779xx pin and ball definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F777xx						STM32F778Ax STM32F779xx									
LQFP100	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216	WLCSP180[1]	LQFP176	LQFP208	TFBGA216						
91	135	A6	163	194	A8	A9	163	194	A8	PB5	I/O	FT	-	UART5_RX, TIM3_CH2, I2C1_SMBA, SPI1_MOSI/I2S1_SD, SPI3_MOSI/I2S3_SD, SPI6_MOSI, CAN2_RX, OTG_HS_ULPI_D7, ETH_PPS_OUT, FMC_SDCKE1, DCMI_D10, LCD_G7, EVENTOUT	-
92	136	B6	164	195	B6	B9	164	195	B6	PB6	I/O	FT	-	UART5_TX, TIM4_CH1, HDMI_CEC, I2C1_SCL, DFSDM1_DATIN5, USART1_TX, CAN2_TX, QUADSPI_BK1_NCS, I2C4_SCL, FMC_SDNE1, DCMI_D5, EVENTOUT	-
93	137	B5	165	196	B5	C8	165	196	B5	PB7	I/O	FT	-	TIM4_CH2, I2C1_SDA, DFSDM1_CKIN5, USART1_RX, I2C4_SDA, FMC_NL, DCMI_VSYNC, EVENTOUT	-
94	138	D6	166	197	E6	A10	166	197	E6	BOOT0	I	B	-	-	VPP
95	139	A5	167	198	A7	E9	167	198	A7	PB8	I/O	FT	-	I2C4_SCL, TIM4_CH3, TIM10_CH1, I2C1_SCL, DFSDM1_CKIN7, UART5_RX, CAN1_RX, SDMMC2_D4, ETH_MII_TXD3, SDMMC1_D4, DCMI_D6, LCD_B6, EVENTOUT	-

4 Memory mapping

The memory map is shown in *Figure 21*.

Figure 21. Memory map

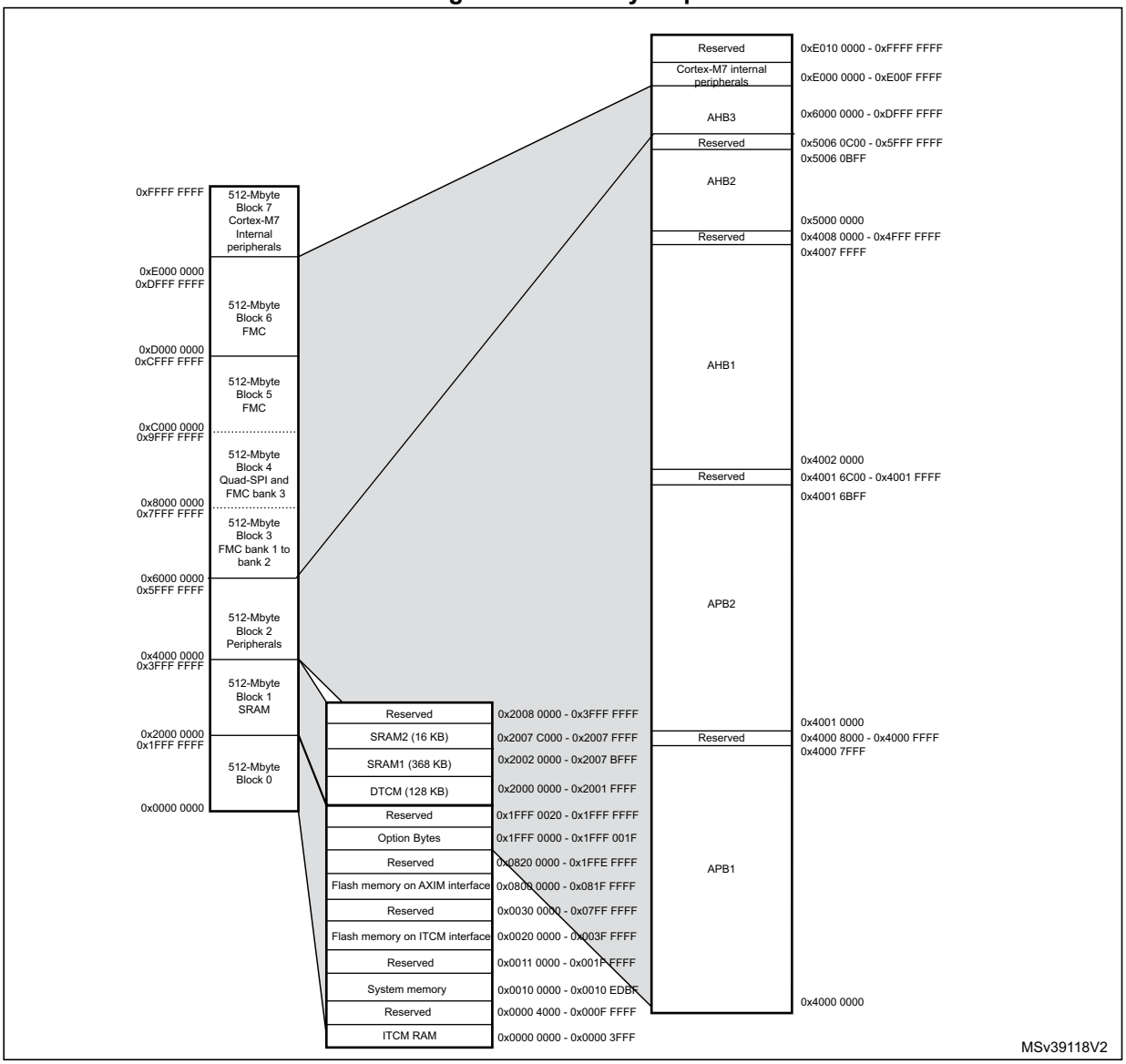


Table 22. Reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	V
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	V
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	V
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	V
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	V
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	V
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	V
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	V
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	V
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	V
		PLS[2:0]=101 (falling edge)	2.65	2.84	2.92	V
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	V
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	V
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	V
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	V
$V_{PVDhyst}$(1)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	V
$V_{PDRhyst}$(1)	PDR hysteresis	-	-	40	-	mV
V_{BOR1}	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	V
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	V
		Rising edge	2.53	2.59	2.63	V
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	V
		Rising edge	2.85	2.92	2.97	V
$V_{BORhyst}$(1)	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPO}$(1)(2)	POR reset temporization	-	0.5	1.5	3.0	ms
I_{RUSH}(1)	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	250	mA
E_{RUSH}(1)	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	V_{DD} = 1.7 V, T_A = 105 °C, I_{RUSH} = 171 mA for 31 µs	-	-	5.4	µC

Table 31. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Single bank mode, ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator OFF

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ		Max(1)						Unit
						TA= 25 °C		TA= 85 °C		TA= 105 °C		
				IDD12	IDD	IDD12	IDD	IDD12	IDD	IDD12	IDD	
IDD12/ IDD	Supply current in RUN mode from V12 and VDD supply	All Peripherals Enabled(2)(3)	180	152	1	167	2	200	2	220	2	mA
			168	136	1	148	2	179	2	198	2	
			144	105	1	115	2	141	2	158	2	
			60	47	1	53	2	79	2	96	2	
			25	22	1	27	2	53	2	70	2	
		All Peripherals Disabled(3)	180	74	1	83	2	116	2	136	2	
			168	65	1	73	2	104	2	123	2	
			144	50	1	57	2	83	2	100	2	
			60	22	1	27	2	53	2	70	2	
			25	10	1	14	2	41	2	58	2	

1. Guaranteed by characterization results.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 32. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Dual bank mode, ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator OFF

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ		Max(1)						Unit
						TA= 25 °C		TA= 85 °C		TA= 105 °C		
				IDD12	IDD	IDD12	IDD	IDD12	IDD	IDD12	IDD	
IDD12/ IDD	Supply current in RUN mode from V12 and VDD supply	All Peripherals Enabled(2)(3)	180	152	1	167	2	200	2	220	2	mA
			168	136	1	148	2	179	2	198	2	
			144	105	1	115	2	141	2	158	2	
			60	47	1	53	2	79	2	96	2	
			25	22	1	27	2	53	2	70	2	
		All Peripherals Disabled(3)	180	74	1	82	2	114	2	137	2	
			168	65	1	73	2	104	2	123	2	
			144	50	1	57	2	83	2	100	2	
			60	22	1	27	2	53	2	70	2	
			25	10	1	14	2	41	2	58	2	

Table 39. Peripheral current consumption

Peripheral		I_{DD}(Typ)(1)			Unit
		Scale 1	Scale 2	Scale 3	
AHB1 (up to 216 MHz)	GPIOA	2.9	2.8	2.2	µA/MHz
	GPIOB	3.0	2.9	2.2	
	GPIOC	2.9	2.8	2.2	
	GPIOD	3.1	3.0	2.3	
	GPIOE	3.1	3.0	2.3	
	GPIOF	2.9	2.8	2.2	
	GPIOG	2.9	2.8	2.2	
	GPIOH	3.1	3.1	2.4	
	GPIOI	3.0	2.9	2.2	
	GPIOJ	2.9	2.9	2.2	
	GPIOK	2.8	2.8	2.4	
	CRC	1.0	0.9	0.8	
	BKPSRAM	0.9	0.9	0.7	
	DMA1	3.17 x N + 11.63	3.08 x N + 11.39	2.6 x N + 9.64	
	DMA2	3.33 x N + 12.84	3.27 x N + 11.84	2.75 x N + 10.10	
	DMA2D	77.7	76.3	63.5	
	ETH_MAC ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	40.1	39.5	32.8	
	OTG_HS	58.5	57.4	48.1	
	OTG_HS+ULPI	58.5	57.4	48.1	
AHB2 (up to 216 MHz)	DCMI	2.9	2.8	2.1	µA/MHz
	JPEG	74.8	73.4	61.9	
	CRYP	1.9	1.7	1.4	
	HASH	4.5	4.4	3.6	
	RNG	6.7	6.7	5.4	
	USB_OTG_FS	32.4	31.9	26.7	
AHB3 (up to 216 MHz)	FMC	18.6	18.2	15.1	µA/MHz
	QSPI	22.3	21.8	18.1	
Bus matrix(2)		3.94	3.25	2.12	µA/MHz

Table 44. LSE oscillator characteristics (f_{LSE} = 32.768 kHz) (1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_m_crit_max	Maximum critical crystal g_m	LSEDRV[1:0]=00 Low drive capability	-	-	0.48	µA/V
		LSEDRV[1:0]=10 Medium low drive capability	-	-	0.75	
		LSEDRV[1:0]=01 Medium high drive capability	-	-	1.7	
		LSEDRV[1:0]=11 High drive capability	-	-	2.7	
t_{SU}(2)	start-up time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design.
2. Guaranteed by characterization results. t_{SU} is the start-up time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 31. Typical application with a 32.768 kHz crystal

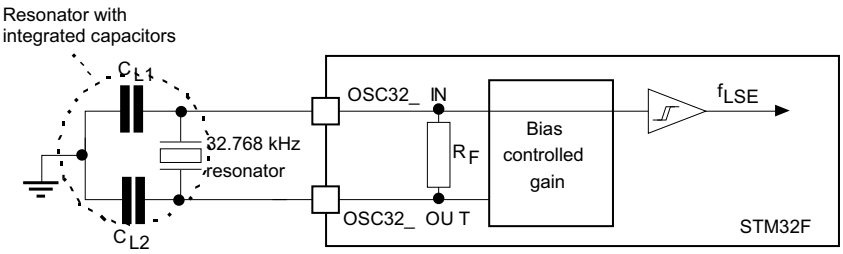


Table 51. MIPI D-PHY characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Output low level voltage	-	1.1	1.2	1.2	V
$V_{IL-ULPS}$	Output high level voltage	-	-50	-	50	mV
V_{IH}	Output impedance of LP transmitter	-	110	-	-	Ω
V_{hys}	15%-85% rise and fall time	-	-	-	25	ns
LP Contention Detector Characteristics						
V_{ILCD}	Logic 0 contention threshold	-	-	-	200	mV
V_{IHCD}	Logic 0 contention threshold	-	450	-	-	

1. Guaranteed based on test during characterization.

Table 52. MIPI D-PHY AC characteristics LP mode and HS/LP transitions(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{LPX}	Transmitted length of any Low-Power state period	-	50	-	-	ns
$T_{CLK-PREPARE}$	Time that the transmitter drives the Clock Lane LP-00 Line state immediately before the HS-0 Line state starting the HS transmission.	-	38	-	95	
$T_{CLK-PREPARE}$ + $T_{CLK-ZERO}$	Time that the transmitter drives the HS-0 state prior to starting the clock.	-	300	-	-	
$T_{CLK-PRE}$	Time that the HS clock shall be driven by the transmitter prior to any associated Data Lane beginning the transition from LP to HS mode.	-	8	-	-	UI

Table 56. Flash memory programming (single bank configuration nDBANK=1) (continued)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{prog}	Programming voltage	32-bit program operation	2.7	-	3	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.7	-	3.6	V

1. Guaranteed by characterization results.
2. The maximum programming time is measured after 100K erase operations.

Table 57. Flash memory programming (dual bank configuration nDBANK=0)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	250	600	
		Program/erase parallelism (PSIZE) = x 32	-	200	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1100	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	800	1400	
		Program/erase parallelism (PSIZE) = x 32	-	500	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2.1	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.5	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	16	32	s
		Program/erase parallelism (PSIZE) = x 16	-	11	22	
		Program/erase parallelism (PSIZE) = x 32	-	8	16	

The SDA and SCL I/O requirements are met with the following restrictions:

- The SDA and SCL I/O pins are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.
- The 20mA output drive requirement in Fast-mode Plus is not supported. This limits the maximum load Cload supported in Fm+, which is given by these formulas:

  $Tr(SDA/SCL)=0.8473xR_pxC_{load}$

  $R_p(min)= (VDD-V_{OL}(max))/I_{OL}(max)$

Where Rp is the I2C lines pull-up. Refer to Section 5.3.20: I/O port characteristics for the I2C I/Os characteristics.

All I^2C SDA and SCL I/Os embed an analog filter. Refer to *Table 84* for the analog filter characteristics:

Table 84. I2C analog filter characteristics(1)

Symbol	Parameter	Min	Max	Unit
t_{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	50(2)	70(3)	ns

1. Guaranteed by characterization results.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered.

Table 111. Synchronous non-multiplexed PSRAM write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{(CLK)}$	FMC_CLK period	$2T_{HCLK} - 0.5$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2	
$t_{(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	$T_{HCLK} + 0.5$	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0.5	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	2.5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	T_{HCLK}	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	1.5	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK} + 1$	-	
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	3.5	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	-	2	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK} + 1$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

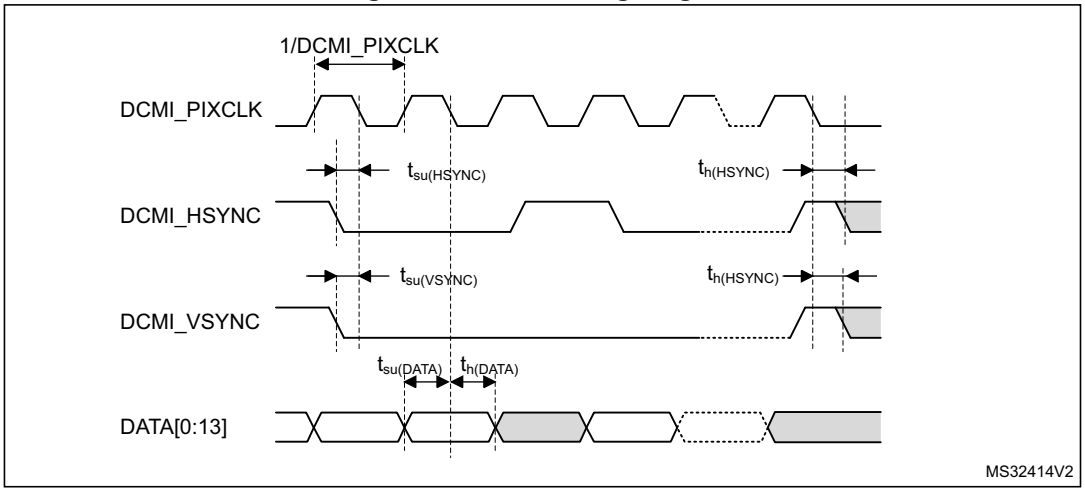
NAND controller waveforms and timings

Figure 69 through *Figure 72* represent synchronous waveforms, and *Table 112* and *Table 113* provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01;
- COM.FMC_WaitSetupTime = 0x03;
- COM.FMC_HoldSetupTime = 0x02;
- COM.FMC_HiZSetupTime = 0x01;
- ATT.FMC_SetupTime = 0x01;
- ATT.FMC_WaitSetupTime = 0x03;
- ATT.FMC_HoldSetupTime = 0x02;
- ATT.FMC_HiZSetupTime = 0x01;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 77. DCMI timing diagram



5.3.33 LCD-TFT controller (LTDC) characteristics

Unless otherwise specified, the parameters given in *Table 121* for LCD-TFT are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage summarized in *Table 17*, with the following configuration:

- LCD_CLK polarity: high
- LCD_DE polarity: low
- LCD_VSYNC and LCD_HSYNC polarity: high
- Pixel formats: 24 bits

Table 121. LTDC characteristics (1)

Symbol	Parameter	Min	Max	Unit
f_{CLK}	LTDC clock output frequency	-	65	MHz
D_{CLK}	LTDC clock output duty cycle	45	55	%
$t_{w(CLKH)}$, $t_{w(CLKL)}$	Clock High time, low time	tw(CLK)/2−0.5	tw(CLK)/2+0.5	ns
$t_{v(DATA)}$	Data output valid time	-	6	
$t_{h(DATA)}$	Data output hold time	0	-	
$t_{v(HSYNC)}$, $t_{v(VSYNC)}$, $t_{v(DE)}$	HSYNC/VSYNC/DE output valid time	-	3.5	
$t_{h(HSYNC)}$, $t_{h(VSYNC)}$, $t_{h(DE)}$	HSYNC/VSYNC/DE output hold time	0.5	-	

1. Guaranteed by characterization results.

5.3.36 SD/SDIO MMC card host interface (SDMMC) characteristics

Unless otherwise specified, the parameters given in *Table 123* for the SDIO/MMC interface are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 5.3.20: I/O port characteristics* for more details on the input/output characteristics.

Figure 81. SDIO high-speed mode

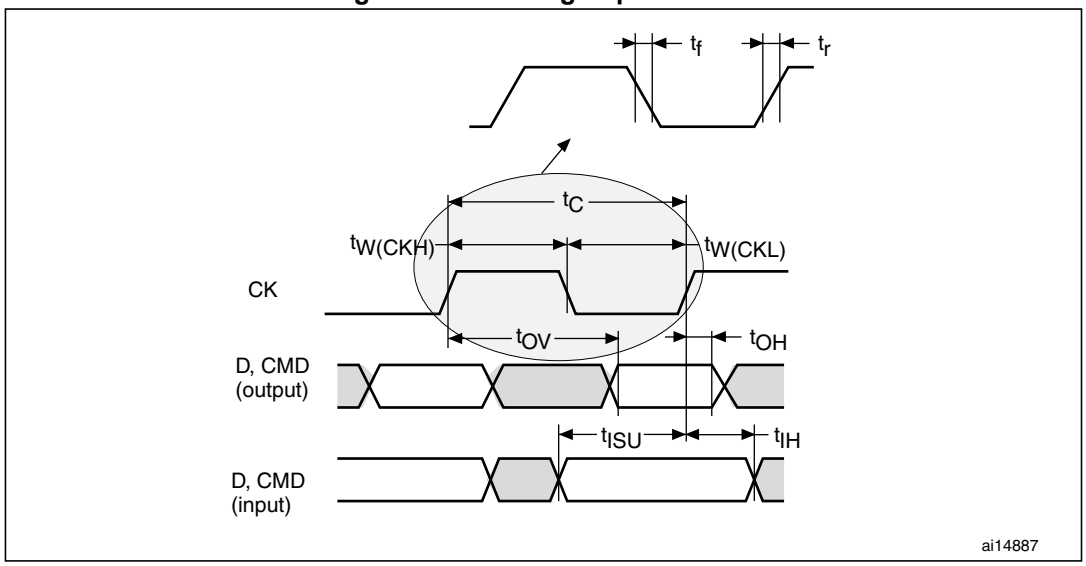


Figure 82. SD default mode

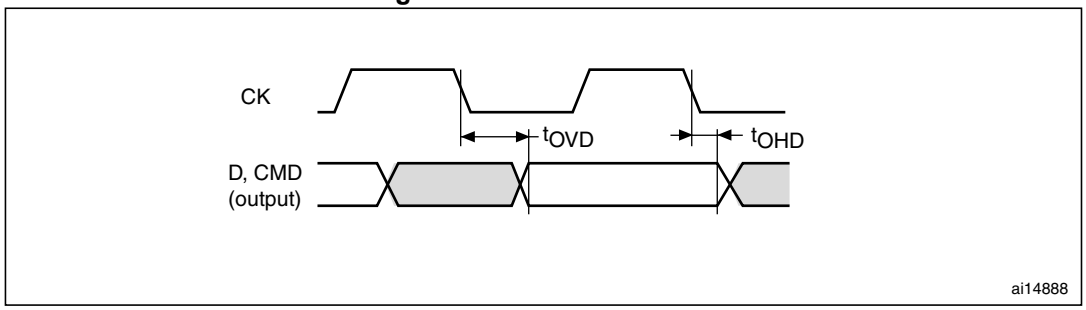


Table 123. Dynamic characteristics: SD / MMC characteristics, V_{DD}=2.7V to 3.6V(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDMMC_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp =50 MHz	9.5	10.5	-	ns
$t_{W(CKH)}$	Clock high time	fpp =50 MHz	8.5	9.5	-	
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t_{ISU}	Input setup time HS	fpp =50 MHz	3.5	-	-	ns
t_{IH}	Input hold time HS	fpp =50 MHz	2.5	-	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t_{OV}	Output valid time HS	fpp =50 MHz	-	11	12	ns
t_{OH}	Output hold time HS	fpp =50 MHz	9	-	-	
CMD, D inputs (referenced to CK) in SD default mode						
tISUD	Input setup time SD	fpp =25 MHz	3.5	-	-	ns
tIHD	Input hold time SD	fpp =25 MHz	2.5	-	-	
CMD, D outputs (referenced to CK) in SD default mode						
tOVD	Output valid default time SD	fpp =25 MHz	-	0.5	1.5	ns
tOHD	Output hold default time SD	fpp =25 MHz	0	-	-	

1. Guaranteed by characterization results.

Table 124. Dynamic characteristics: eMMC characteristics, V_{DD}=1.71V to 1.9V(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDMMC_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp =50 MHz	9.5	10.5	-	ns
$t_{W(CKH)}$	Clock high time	fpp =50 MHz	8.5	9.5	-	
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	fpp =50 MHz	3	-	-	ns
t_{IH}	Input hold time HS	fpp =50 MHz	4	-	-	
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	fpp =50 MHz	-	11	15.5	ns
t_{OH}	Output hold time HS	fpp =50 MHz	9.5	-	-	

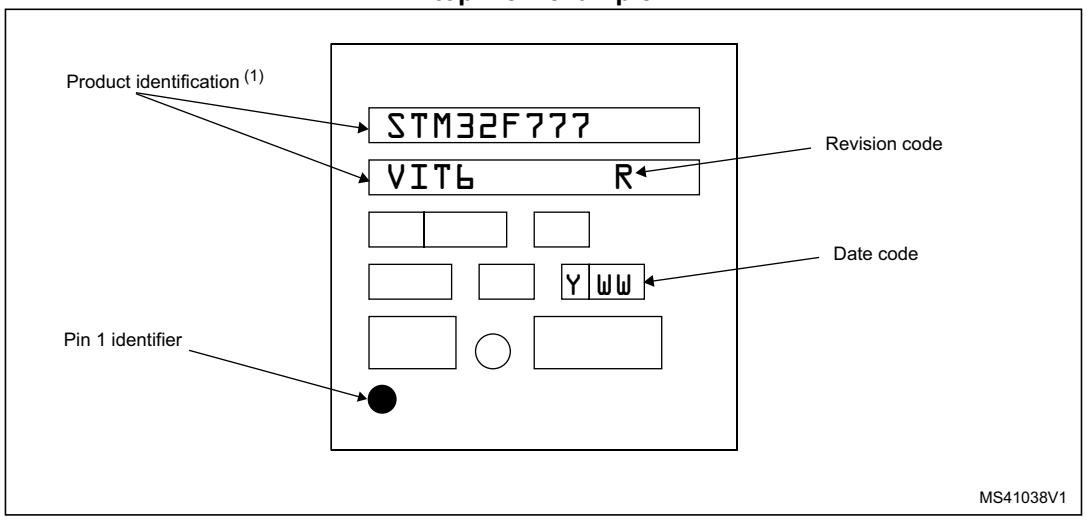
1. Guaranteed by characterization results.
2. Cload = 20 pF.

LQFP100 device making

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 85. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package top view example



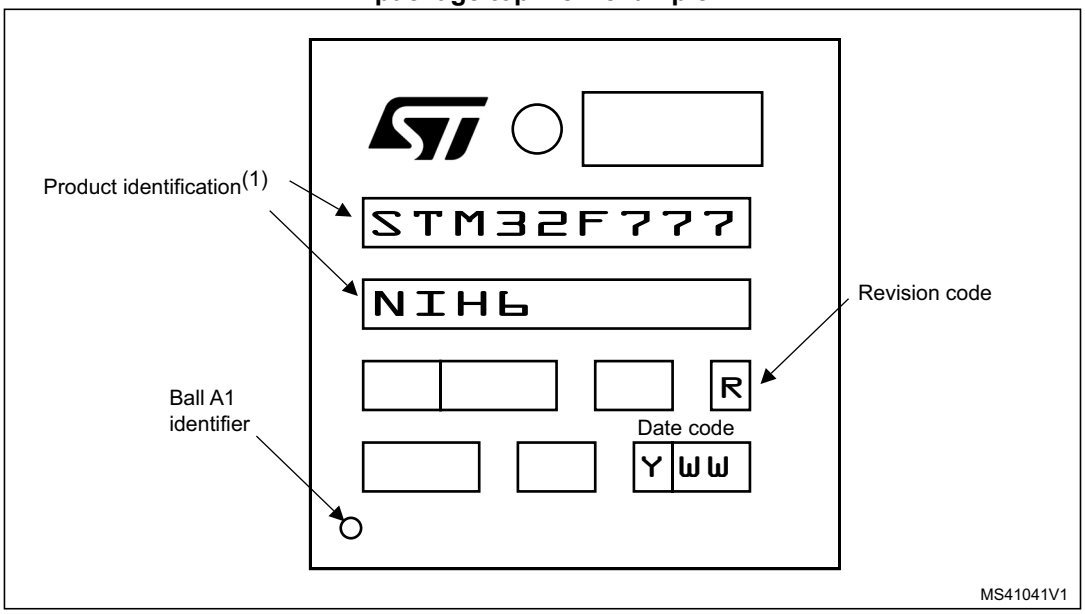
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

TFBGA216 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 103. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package top view example



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.